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List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Spatially Resolved Mapping of Electrical Conductivity across Individual Domain (Grain) Boundaries in Graphene. ACS Nano, 2013, 7, 7956-7966.	14.6	124
2	Comparison of graphene formation on C-face and Si-face SiC {0001} surfaces. Physical Review B, 2010, 82, .	3.2	76
3	Atomic-Scale Mapping of Thermoelectric Power on Graphene: Role of Defects and Boundaries. Nano Letters, 2013, 13, 3269-3273.	9.1	52
4	Graphene formed on SiC under various environments: comparison of Si-face and C-face. Journal Physics D: Applied Physics, 2012, 45, 154001.	2.8	44
5	Energy Gap Induced by Friedel Oscillations Manifested as Transport Asymmetry at Monolayer-Bilayer Graphene Boundaries. Physical Review X, 2014, 4, .	8.9	39
6	Size, shape, composition, and electronic properties of InAs/GaAs quantum dots by scanning tunneling microscopy and spectroscopy. Journal of Applied Physics, 2010, 108, 114315.	2.5	32
7	Interface structure of graphene on SiC(000 <mml:math) (xr<br="" 0.784314="" 1="" 10="" 50="" 512="" etqq1="" overlock="" rgbt="" td="" tf="" tj="">Physical Review B. 2012. 85</mml:math)>	nlns:mml= 3.2	"http://www 27
8	Electronic states of InAs/GaAs quantum dots by scanning tunneling spectroscopy. Applied Physics Letters, 2010, 97, 123110.	3.3	11
9	Formation of a Buffer Layer for Graphene on C-Face SiC{0001}. Journal of Electronic Materials, 2014, 43, 819-827.	2.2	4
10	Formation of graphene atop a Si adlayer on the C-face of SiC. Physical Review Materials, 2019, 3, .	2.4	3
11	Formation of graphene on SiC(0001Â ⁻) surfaces in disilane and neon environments. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 04E102.	1.2	2
12	Characteristics of graphene for quantized hall effect measurements. , 2012, , .		2